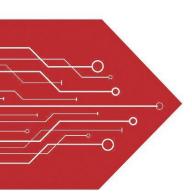
MSKSEMI















ESD

TVS

TSS

MOV

GDT

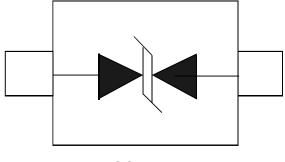
PLED

Broduct data speet





- 480Watts peak pulse power (tp =8/20µs)
- Bidirectional configurations
- Solid-state silicon-avalanche technology
- Low clamping voltage
- Low leakage current
- IEC 61000-4-2 ±30kV contact ±30kVair
- IEC 61000-4-4 (EFT) 40A (5/50ns)
- IEC 61000-4-5 (Lightning) 20A(8/20µs)



SOD-323

»Applications

- Microprocessor based equipment
- Personal Digital Assistants (PDA's)
- Notebooks, Desktops, and Servers
- Portable Instrumentation
- Pagers Peripherals



»Mechanical Data

- SOD323 package
- Molding compound flammability rating: UL 94V-0
- Packaging: Tape and Reel
- RoHS/WEEE Compliant

Absolute Maximum Rating

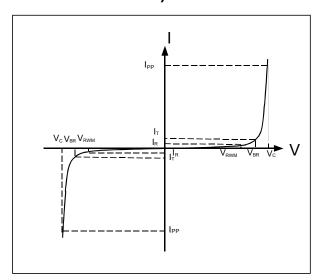
Absolute maximum Nating				
Rating	Symbol	Value	Units	
Peak Pulse Power (t _p =8/20μs)	P _{PP}	480	Watts	
Peak Pulse Current (t _p =8/20µs) (note1)	I _{pp}	20	А	
ESD per IEC 61000-4-2(Air) ESD per IEC 61000-4-2(Contact)	V _{ESD}	30 30	kV	
Lead Soldering Temperature	TL	260(10seconds)	°C	
Junction Temperature	TJ	-55 to + 150	°C	
Storage Temperature	T _{stg}	-55 to + 150	°C	

Electrical Characteristics

Parameter	Symbol	Conditions	Min	Typical	Max	Units
Reverse Stand-OffVoltage	V_{RWM}				3.3	V
Reverse Breakdown Voltage	V_{BR}	I _T =1mA	4.0			V
Reverse LeakageCurrent	I _R	V _{RWM} =3.0V,T=25℃			1	uA
Clamping Voltage	Vc	I _{PP} =20A,t _p =8/20μs			24	V
Junction Capacitance	C _j	V _R = 0V, f =1MHz		100		pF

Electrical Parameters (TA = 25°C unless otherwisenoted)

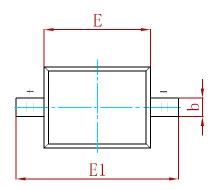
Symbol	Parameter
I _{PP}	Maximum Reverse Peak Pulse Current
Vc	Clamping Voltage @ I _{PP}
V _{RWM}	Working Peak Reverse Voltage
I _R	Maximum Reverse Leakage Current @ V _{RWM}
V_{BR}	Breakdown Voltage @ I⊤
lτ	Test Current

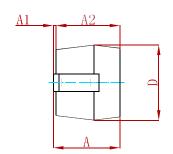


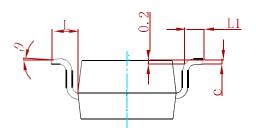
Note: 8/20µs pulsewaveform.



PACKAGE MECHANICAL DATA

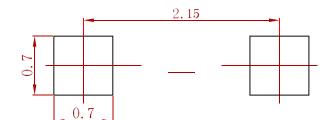






Ob. a. l	Dimensions In Millimeters		Dimensions In Inches	
Symbol	Min.	Max.	Min.	Max.
Α		1.000		0.039
A 1	0.000	0.100	0.000	0.004
A2	0.800	0.900	0.031	0.035
b	0.250	0.350	0.010	0.014
С	0.080	0.150	0.003	0.006
D	1.200	1.400	0.047	0.055
E	1.600	1.800	0.063	0.071
E1	2.550	2.750	0.100	0.108
L	0.47	REF.	0.019	REF.
L1	0.250	0.400	0.010	0.016
θ	0°	8°	0°	8°

Suggested Pad Layout



Note:

- 1.Controlling dimension:in millimeters.
- 2.General tolerance:± 0.05mm.
- 3. The pad layout is for reference purposes only.

REEL SPECIFICATION

P/N	PKG	QTY
PESD3V3L1BA-MS	SOD-323	3000



Semiconductor

Compiance

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